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DM54S189/DM74S189 64-Bit (16 x 4) TRI-STATE® RAM DM54S189A/DM74S189A High Speed 64-Bit TRI-STATE RAM

General Description

These 64-bit active-element memories are monolithic Schottky-clamped transistor-transistor logic (TTL) arrays organized as 16 words of 4 bits each. They are fully decoded and feature a chip-enable input to simplify decoding required to achieve the desired system organization. The memories feature PNP input transistors that reduce the low level input current requirement to a maximum of -0.25 mA, only one-eighth that of a DM74S standard load factor. The chip-enable circuitry is implemented with minimal delay times to compensate for added system decoding.

The TRI-STATE output combines the convenience of an open-collector with the speed of a totem-pole output; it can be bus-connected to other similar outputs; yet it retains the fast rise time characteristics of the TTL totem-pole output. Systems utilizing data bus lines with a defined pull-up impedance can employ the open-collector DM74S289.

Write Cycle: The complement of the information at the data input is written into the selected location when both the chip-enable input and the read/write input are low. While the read/write input is low, the outputs are in the high-impedance state. When a number of the DM74S189 outputs are bus connected, this high-impedance state will neither load nor drive the bus line, but it will allow the bus line to be driven by another active output or a passive pull-up if desired.

Read Cycle: The stored information (complement of information applied at the data inputs during the write cycle) is

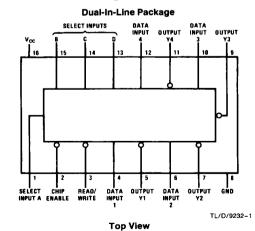
available at the outputs when the read/write input is high and the chip-enable is low. When the chip-enable is high, the outputs will be in the high-impedance state.

The fast access time of the DM74S189A makes it particularly attractive for implementing high-performance memory functions requiring access times less than 25 ns. The high capacitive drive capability of the outputs permits expansion without additional output buffering. The unique functional capability of the DM74S189A outputs being at a high-impedance during writing, combined with the data inputs being inhibited during reading, means that both data inputs and outputs can be connected to the data lines of a bus-organized system without the need for interface circuits.

Features

- Schottky-clamped for high speed applications (S189A)
 Access from chip-enable input
 17 ns max
 Access from address inputs
 25 ns max
- TRI-STATE outputs drive bus-organized systems and/or high capacitive loads (S189, S189A)
- DM74S289 are functionally equivalent and have opencollector outputs
- DM54SXXX is guaranteed for operation over the full military temperature range of −55°C to +125°C
- Compatible with most TTL circuits
- Chip-enable input simplifies system decoding

Connection Diagram



Truth Table

	Inp	uts	
Function	Chip- Enable	Read/ Write	Output
Write (Store Complement of Data)	L	L	High-Impedance
Read	L	Н	Stored Data
Inhibit	Н	Х	High-Impedance

H = High Level, L = Low Level, X = Don't Care

Order Number DM54S189J, DM54S189AJ, DM74S189J, DM74S189AJ, DM74S189N or DM74S189AN See NS Package Number J16A or N16E

	Operating Conditions								
please contact the National Semi	conductor Sales	Supply Voltage (V _{CC}) DM54S189	Min 4.5	Max 5.5	Units V				
Supply Voltage, V _{CC}	7.0V	DM74S189	4.75	5.25	V				
Input Voltage	5.5V	Temperature (T _A)							
Output Voltage	5.5V	DM54S189	-55	+ 125	°C				
Storage Temperature Range	-65°C to +150°C	DM74S189	0	+ 70	°C				
Lead Temperature (Soldering 10 sec.)	+300°C								

DM54S189, DM74S189 Electrical Characteristics over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
V _{IH}	High Level Input Voltage			2			V
V _{IL}	Low Level Input Voltage					0.8	V
V _{OH}	High Level Output Voltage	V _{CC} = Min	$I_{OH} = -2.0 \text{ mA},$ DM54S189	2.4	3.4		v
			$I_{OH} = -6.5 \text{ mA},$ DM74S189	2.4	3.2		v
ICEX	High Level Output Current	V _{CC} = Min	V _{OH} = 2.4V			40	μА
	Open Collector Only		V _{OH} = 5.5V			100	μΛ
VOL	Low Level Output	V _{CC} = Min,	DM54S189			0.5	V
	Voltage	I _{OL} = 16 mA	DM74S189			0.45	٧
lін	High Level Input Current	V _{CC} = Max, V _I = 2.7V				25	·μA
4	High Level Input Current at Maximum Voltage	$V_{CC} = Max, V_I = 5.5V$				1.0	mA
I _{IL}	Low Level Input Current	V _{CC} = Max, V ₁	= 0.45V			- 250	μΑ
los	Short Circuit Output Current (Note 4)	$V_{CC} = Max,$ $V_{O} = 0V$	DM54S189, DM74S189	-30		-100	mA
lcc	Supply Current (Note 5)	V _{CC} = Max			75	110	mA
V _{IC}	Input Clamp Voltage	V _{CC} = Min, l ₁ =	- 18 mA			-1.2	٧
lozн	TRI-STATE Output Current, High Level Voltage Applied	$V_{CC} = Max,$ $V_{O} = 2.4V$	DM54S189, DM74S189			50	μΑ
lozL	TRI-STATE Output Current, Low Level Voltage Applied	$V_{CC} = Max,$ $V_{O} = 0.45V$	DM54S189, DM74S189	-50	i		μΑ
C _{IN}	Input Capacitance	V _{CC} = 5V, V _{IN} = 2V, T _A = 25°C, 1 MHz			4.0		pF
Co	Output Capacitance	V _{CC} = 5V, V _O = 2V, T _A = 25°C, 1 MHz, Output "Off"			6.0		pF

DM74S189 Switching Characteristics over recommended operating ranges of T_A and V_{CC} unless otherwise noted

			Conditions	DM54S189			DM74S189			
Symbol	Para	Parameter		Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	Units
t _{AA}	Access Times from Add	ress	C _L = 30 pF,		25	50		25	35	ns
^t CZH	Output Enable Time to High Level	Access Times from	$R_L = 280\Omega$ (Figure 4)		12	25		12	17	ns
t _{CZL}	Output Enable Time to Low Level	Chip-Enable			12	25		12	17	ns
twzн	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t _{WZL}	Output Enable Time to Low Level				13	35		13	25	ns
^t CHZ	Output Disable Time from High Level	Disable Times from Chip-Enable	$C_L = 5 pF,$ $R_L = 280\Omega$		12	25		12	17	ns
tCLZ	Output Disable Time from Low Level		(Figure 4)		12	25		12	17	ns
t _{WHZ}	Output Disable Time from High Level	Disable Times from			15	35		15	25	ns
^t wLZ	Output Disable Time from Low Level	Read/Write		-	15	35		15	25	ns
t _{WP}	Width of Write Enable P	uise (Read/Write Low)		25			25			ns
tasw	Set-Up Time (Figure 1)	Address to Read/Write		0			0			ns
t _{DSW}		Data to Read/Write		25			25			ns
t _{CSW}		Chip-Enable to Read/Write		0			0			ns
tahw	Hold Time (Figure 1)	Address from Read/Write		0			0			ns
t _{DHW}		Data from Read/Write	,	0			0			ns
tchw		Chip-Enable from Read/Write		0			0			ns

Absolute Maximum Ratir	IGS (Note 1)	Operating Conditions							
If Military/Aerospace specified device please contact the National Semi Office/Distributors for availability and	conductor Sales	Supply Voltage (V _{CC}) DM54S189(A)	Min 4.5	Max 5.5	Units V				
Supply Voltage, V _{CC}	7.0V	DM74S189(A)	4.75	5.25	v				
Input Voltage	5.5V	Temperature (T _A)							
Output Voltage	5.5V	DM54S189(A)	-55	+ 125	°C				
Storage Temperature Range	-65°C to +150°C	DM74S189(A)	0	+70	°C				
l ead Temperature (Soldering 10 sec)	± 300°C								

DM54S189A, DM74S189A Electrical Characteristics over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions			Тур	Max	Units
V _{IH}	High Level Input Voltage		2			V	
V _{IL}	Low Level Input Voltage					0.8	v
V _{OH}	High Level Output Voltage	V _{CC} = Min	$I_{OH} = -2.0 \text{ mA},$ DM54S189A	2.4	3.4		٧
			$I_{OH} = -6.5 \text{ mA},$ DM74S189A	2.4	3.2		٧
VOL	Low Level Output	V _{CC} = Min	I _{OL} = 16 mA			0.45	v
	Voltage		I _{OL} = 20 mA			0.5	1
l _{IH}	High Level Input Current	$V_{CC} = Max, V_I = 2.4V$				10	μΑ
lı .	High Level Input Current at Maximum Voltage	$V_{CC} = Max, V_1 = 5.5V$				1.0	mA
I _{IL}	Low Level Input Current	V _{CC} = Max, V _I = 0.40V				-250	μA
los	Short Circuit Output Current (Note 4)	V _{CC} = Max, V _O = 0V		-20		-90	mA
loc	Supply Current (Note 5)	V _{CC} = Max			75	100	mA
V _{IC}	Input Clamp Voltage	V _{CC} = Min, I _I = -18 mA				-1.2	V
lozн	TRI-STATE Output Current, High Level Voltage Applied	V _{CC} = Max, V _O = 2.4V				40	μА
lozL	TRI-STATE Output Current, Low Level Voltage Applied	$V_{CC} = Max, V_O = 0.4V$		-40			μА
C _{IN}	Input Capacitance	V _{CC} = 5V, V _{IN} = 2V, T _A = 25°C, 1 MHz			4.0		рF
Co	Output Capacitance	$V_{CC} = 5V$, $V_O = 2V$, $T_A = 25^{\circ}C$, 1 MHz, Output "Off"			6.0		pF

DM54S189A, DM74S189A Switching Characteristics over recommended operating ranges of T_A and V_{CC} unless otherwise noted

			Conditions	DM54S189A			DM74S189A			
Symbol	Para	Parameter		Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	Units
t _{AA}	Access Time from Addre	ess	$C_L = 30 pF$,		20	30		20	25	ns
^t CZH	Output Enable Time to High Level	Access Times from Chip-Enable	$R_L = 280\Omega$ (Figure 4)		11	25		11	17	ns
t _{CZL}	Output Enable Time to Low Level				11	25		11	17	ns
twzн	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t _{WZL}	Output Enable Time to Low Level				13	35		13	25	ns
^t CHZ	Output Disable Time from High Level	Disable Times from Chip-Enable	$C_L = 5 pF,$ $R_L = 280\Omega$		12	25		12	17	ns
tclz	Output Disable Time from Low Level		(Figure 4)		12	25		12	17	ns
t _{WHZ}	Output Disable Time from High Level	Disable Times from			15	35		15	25	ns
t _{WLZ}	Output Disable Time from Low Level	Read/Write			15	35		15	25	ns
twp	Width of Write Enable P	ulse (Read/Write Low)		25			20			ns
tasw	Set-Up Time (Figure 1)	Address to Read/Write		0			0			ns
t _{DSW}		Data to Read/Write		25			20	_	·	ns
tcsw		Chip-Enable to Read/Write		0			0			ns
t _{AHW}	Hold Time (Figure 1)	Address from Read/Write		0			0			ns
t _{DHW}		Data from Read/Write		0			0			ns
tchw		Chip-Enable from Read/Write		0			0			ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DM54S189(A) and across the 0°C to +70°C range for the DM74S189(A). All typicals are given for $V_{CC} = 5.0V$ and $T_A = 25^{\circ}C$.

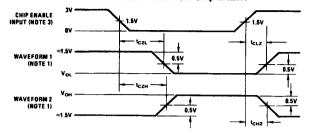
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: ICC is measured with all inputs grounded; and the outputs open.

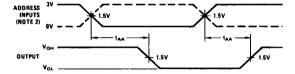
DM54S189(A), DM74S189(A) Switching Time Waveforms

Enable and Disable Time from Chip-Enable



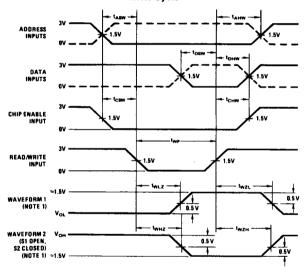
TL/D/9232-2

Access Time from Address Inputs



TL/D/9232-3

Write Cycle



TL/D/9232-4

FIGURE 1

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled. Waveform 2 is for the output with internal conditions such that the output is high except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: t_t ≤ 2.5 ns, t₁ ≤ 2.5 ns, PRR ≤ 1 MHz and $Z_{OUT} = \approx 50\Omega$.